

Application number 09/606,252
Amendment dated June 11, 2003
Reply to final office action

PATENT

Amendments to the Specification:

Please replace the paragraph beginning at page 7, line 7, with the following rewritten paragraph:

E1
FIG. 4 shows a cross-section of a high voltage transistor 400 formed by the technique of the present invention. Transistor 400 has gate region 110, and two source/drain regions 105 separated by a channel region 135. An isolation region 150 separates transistor 400 from other devices in the integrated circuit. Field implants 120 are offset from source/drain regions 105 as described above. Mask region 410 is the mask area defined for formation of well 140. Well 140, field implant 120, and enhancement region 130 (for enhancement transistors) can be formed by implanting at different energy levels, using only the mask defining mask region [140] 410. †

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